

Fig. 1

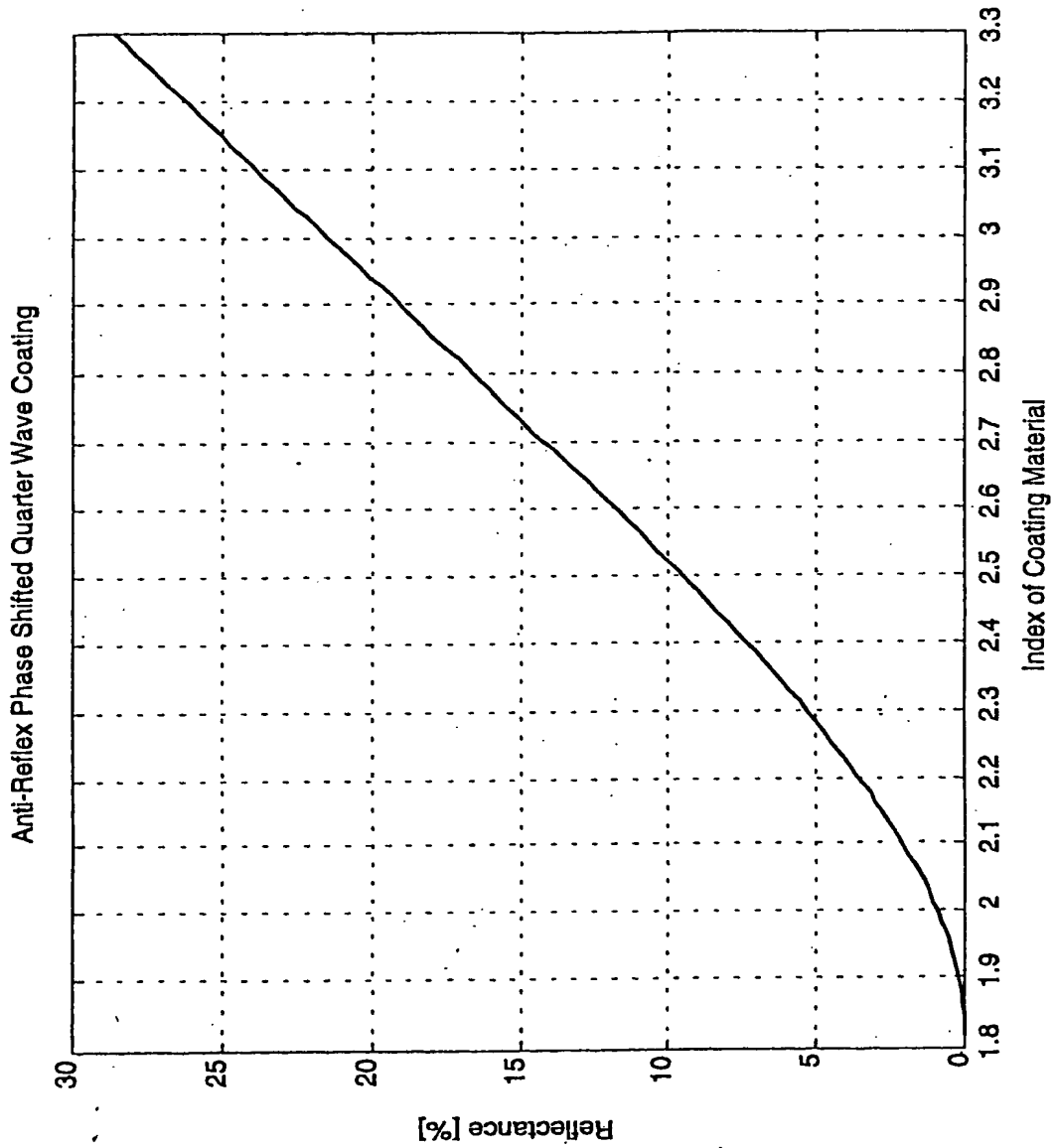


Fig. 2

Fig. 3

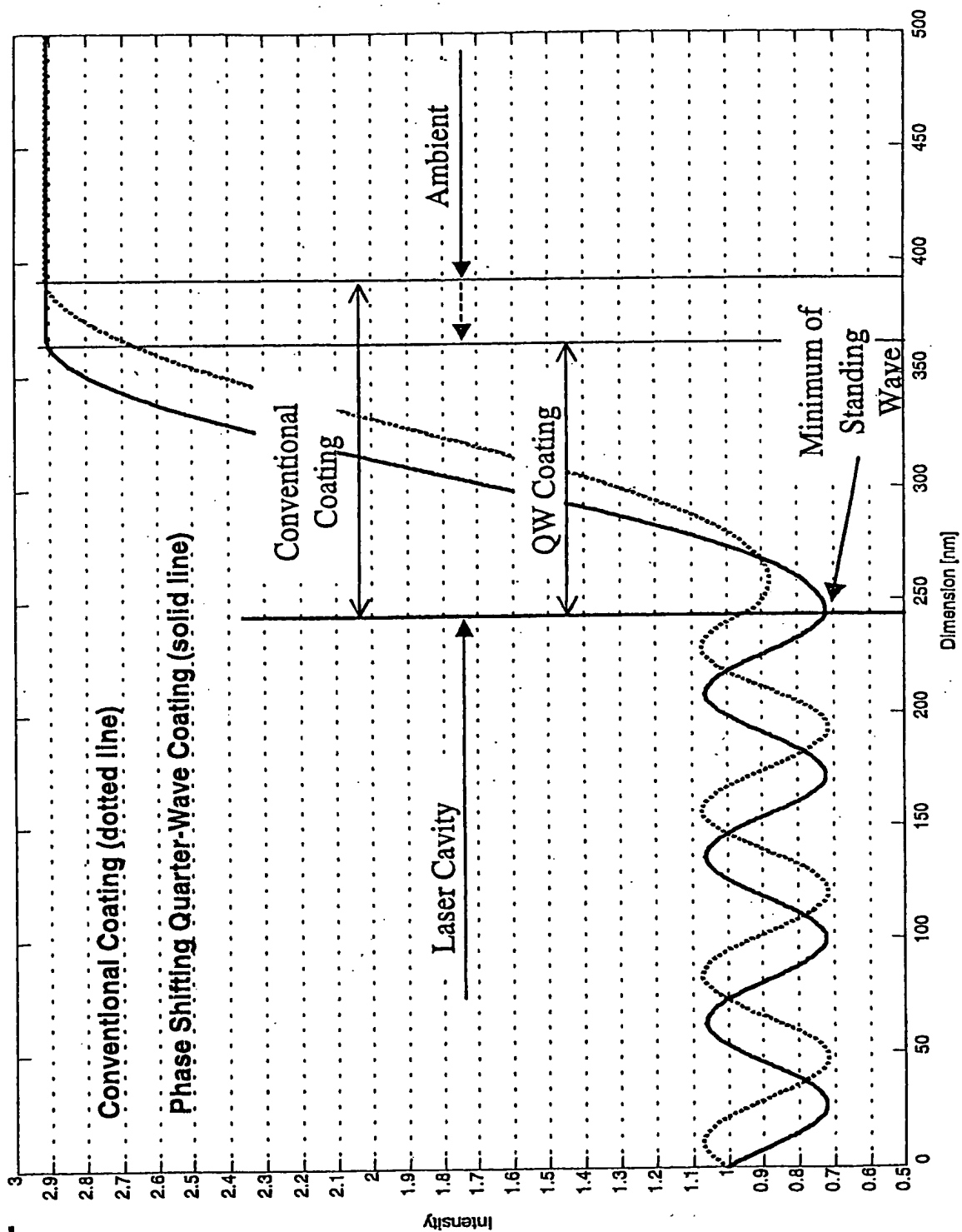


Fig. 4(b)

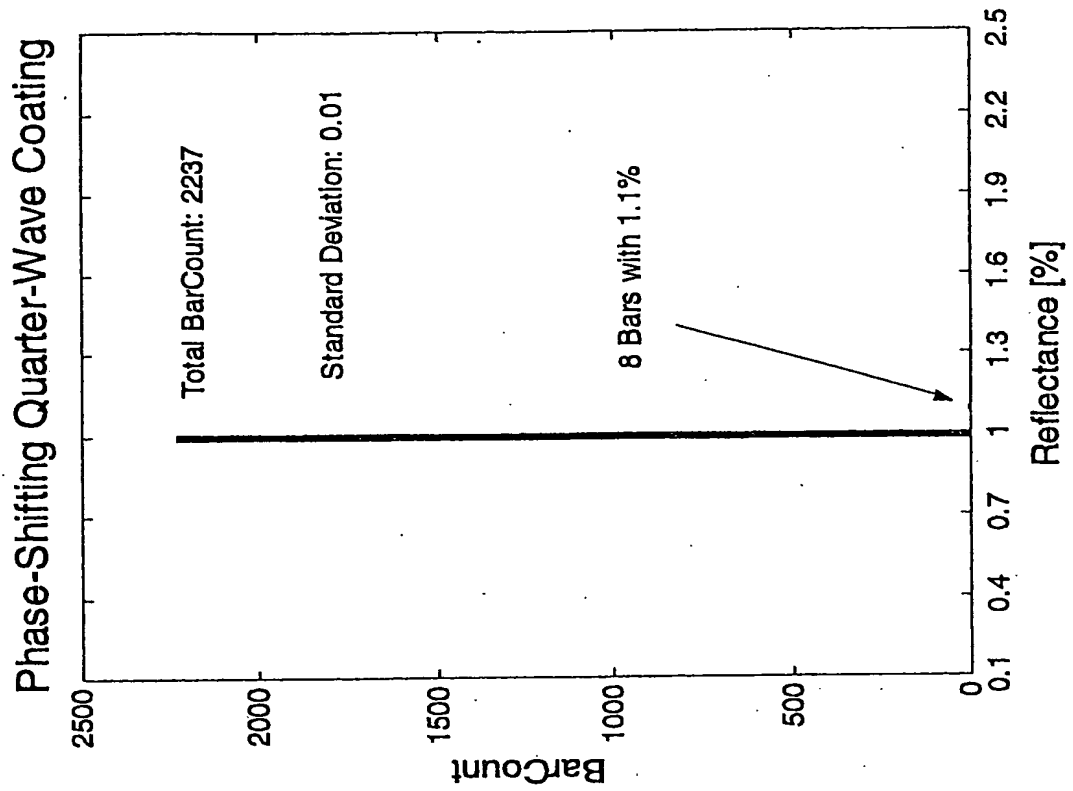


Fig. 4(a)

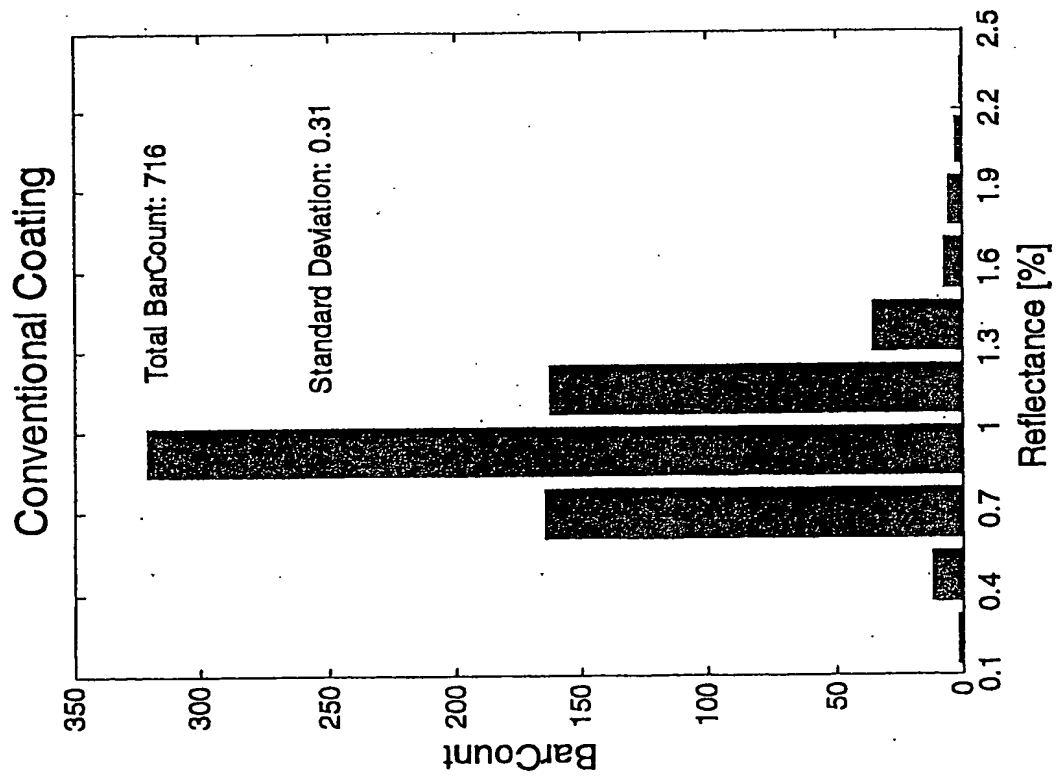
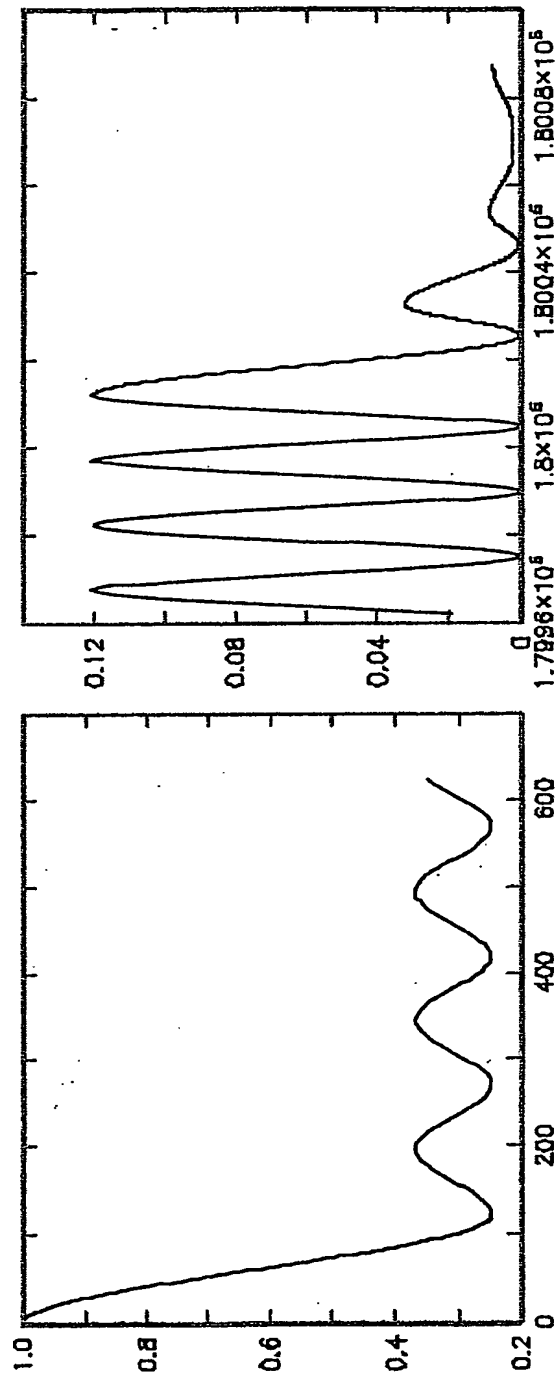
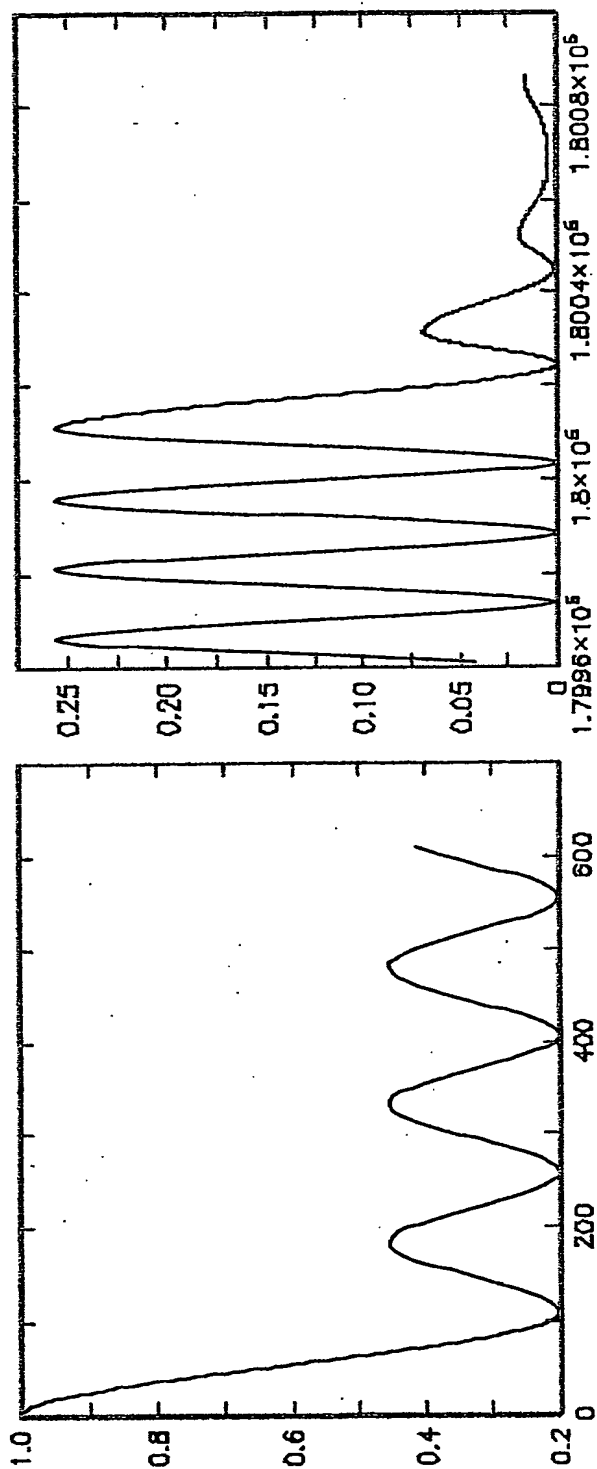


Fig. 5

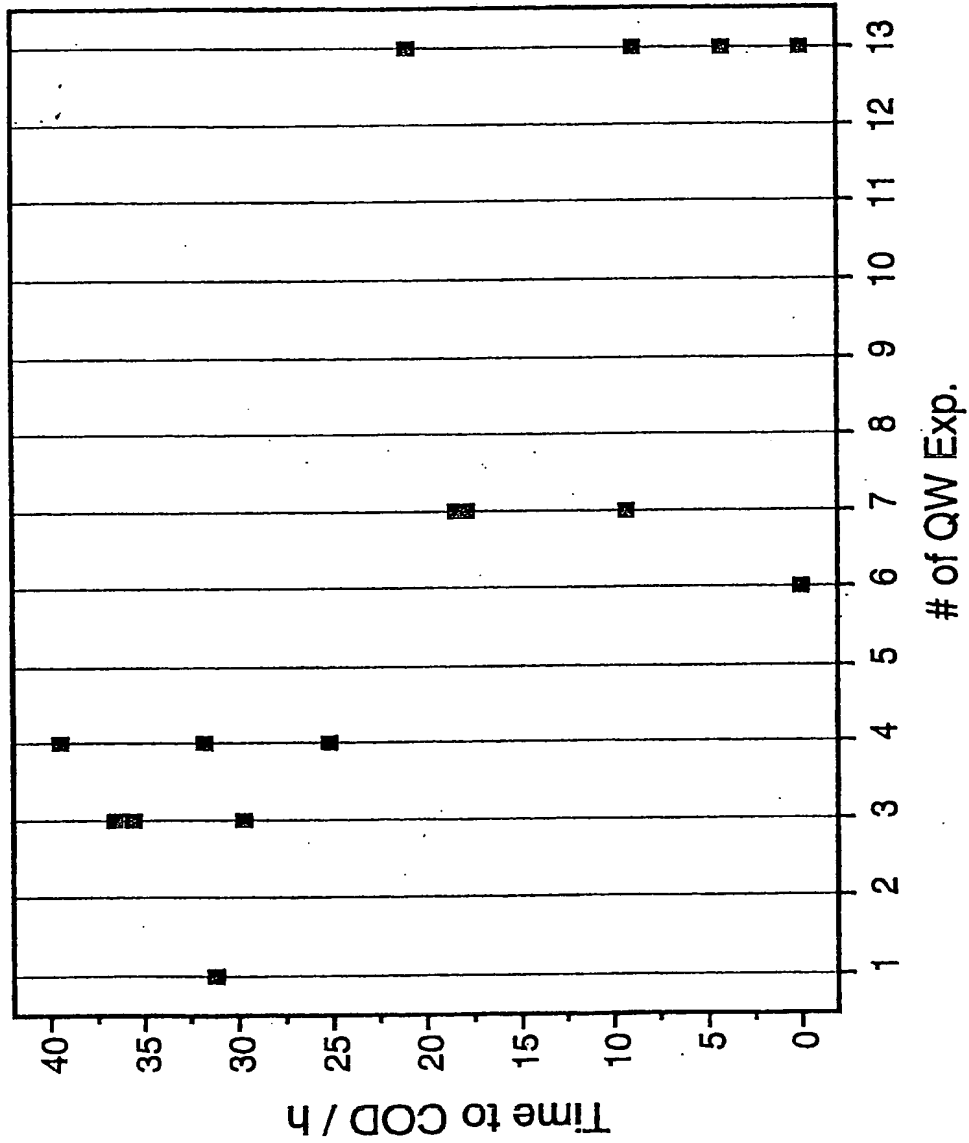


Phase Shifting Quarter Wave Coating with a 1 % Reflectance

Fig. 6



Phase Shifting Quarter Wave Coating with a 4 % Reflectance



Time to COD vs. # of QW Exp

Fig. 7

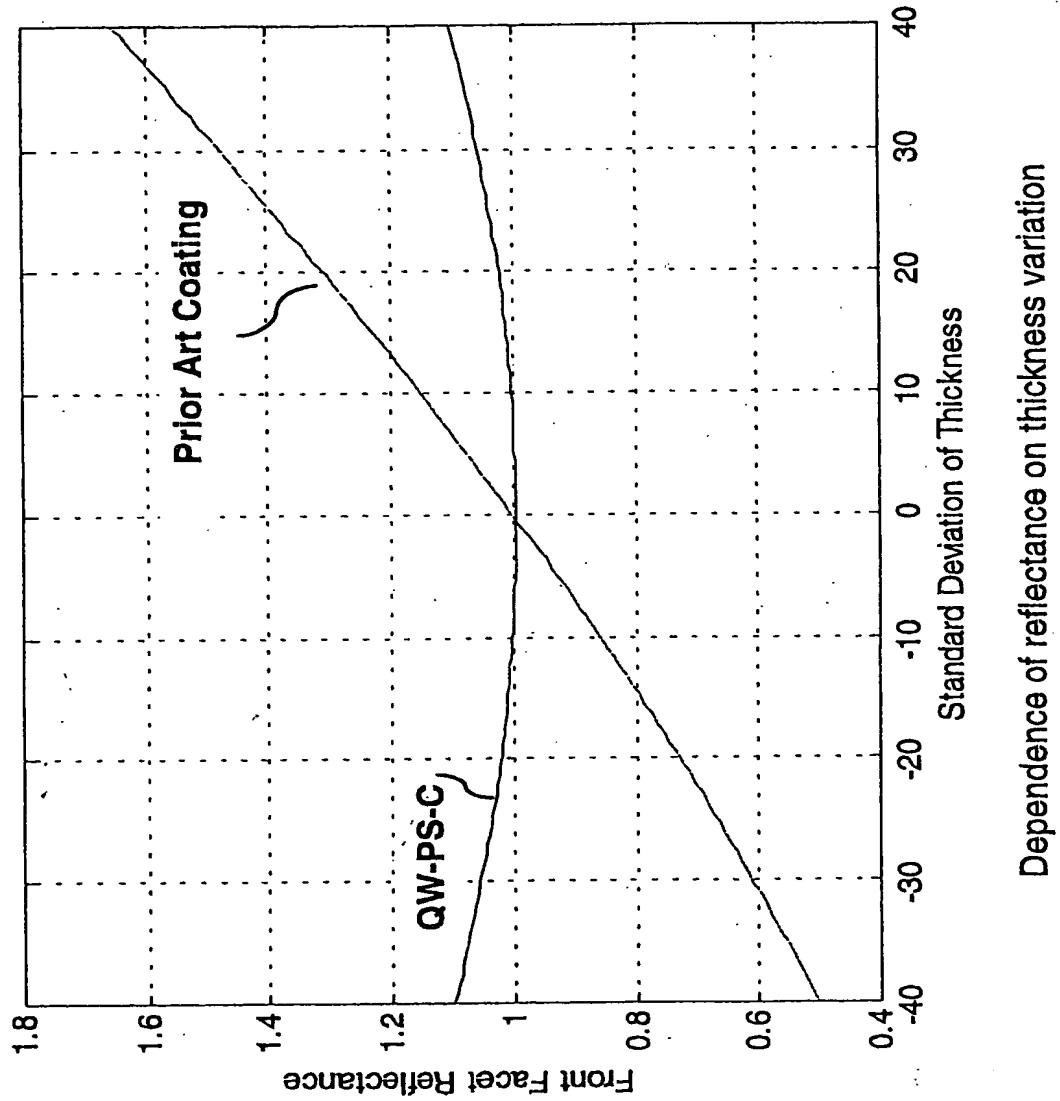
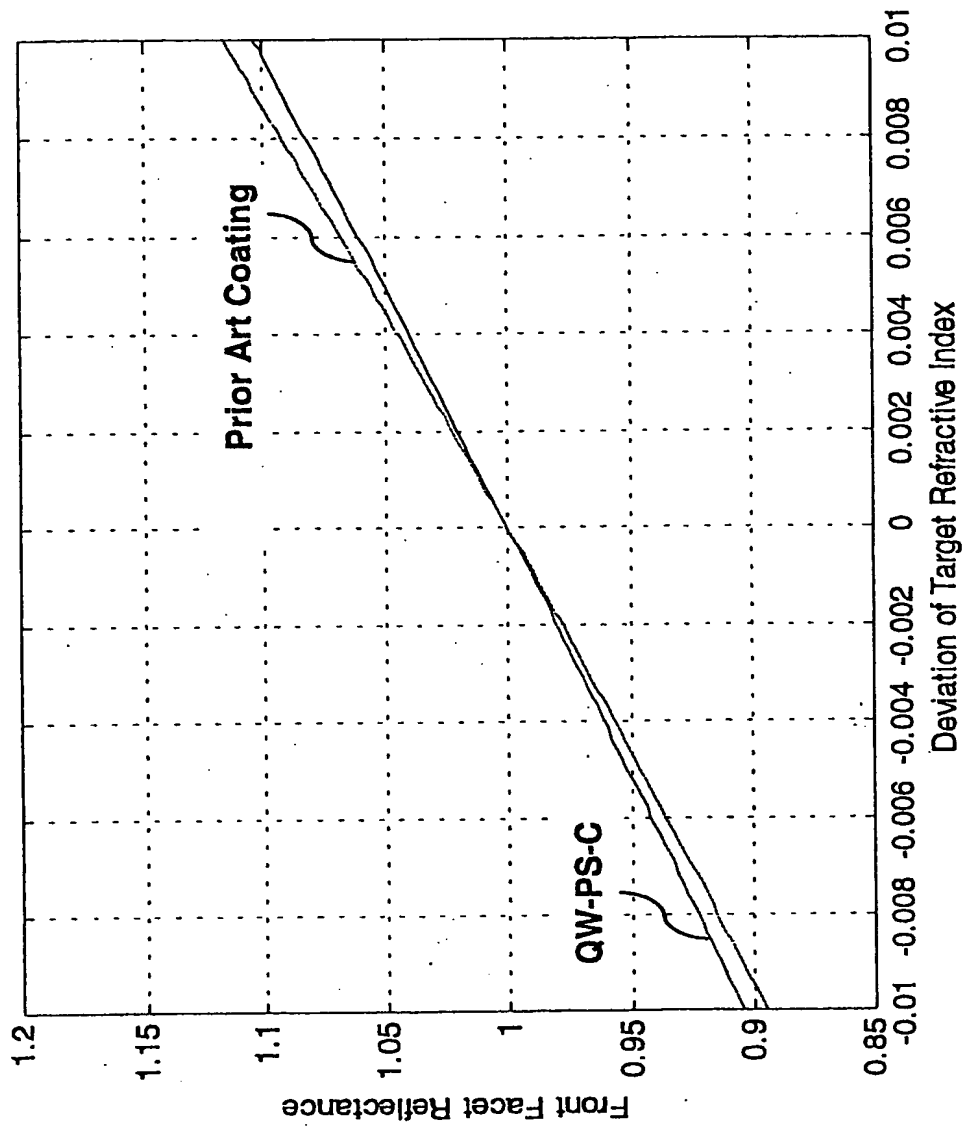


Fig. 9



Dependence of Reflectance on index variation

Fig. 10

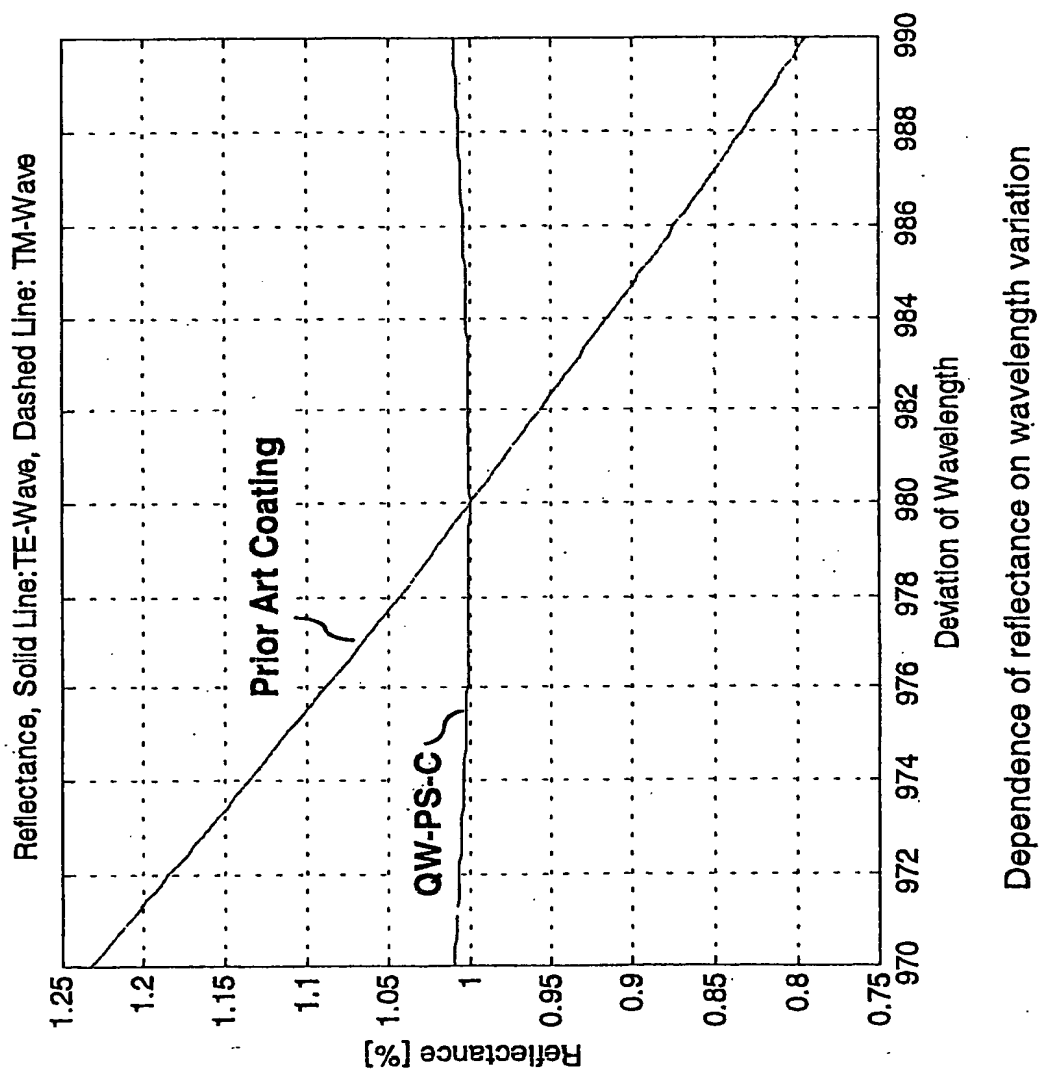


Fig. 11

Process parameters

Reflectivity R	index of refraction n	Substrate Temperature T_s (°C)	Pressure P (Torr)	Plasma Power L_{plasma} (W)	nitrogen flux n_{N_2} (sccm)	ammonia flux n_{NH_3} (sccm)	silane flux(*) n_{SiH_4} (sccm)
0.05%	1.86	300	1.4	25	35	18	236
1%	2.01	300	1.4	25	35	13	403
4%	2.23	300	1.4	25	35	8.5	491
1%(**)	1.83	300	1.4	20	330	11.2	300

(*) precursor gas of 2% SiH₄ diluted in Helium

(**) conventional non- $\lambda/4$ coating

Fig. 12

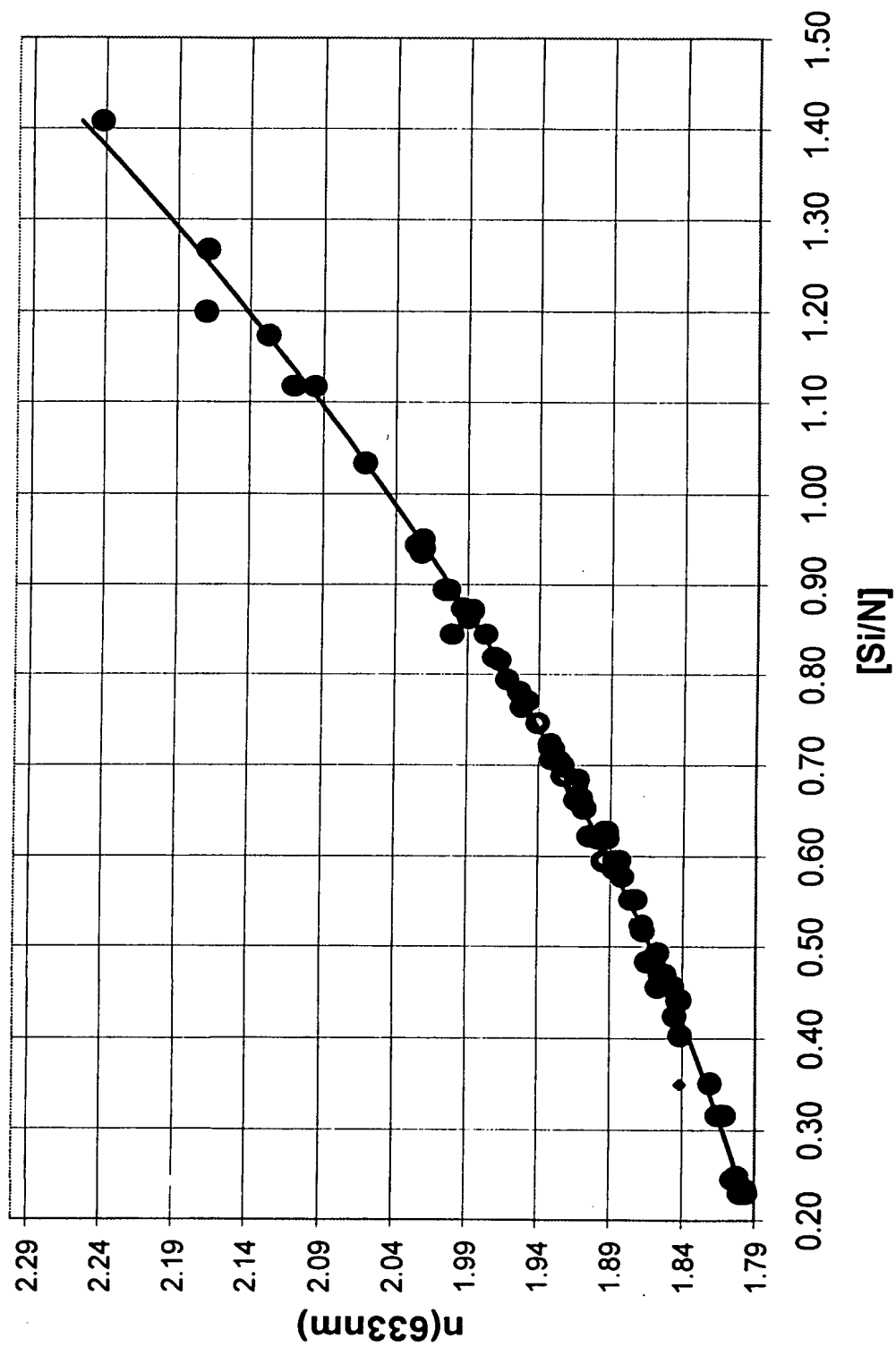


Fig. 13

